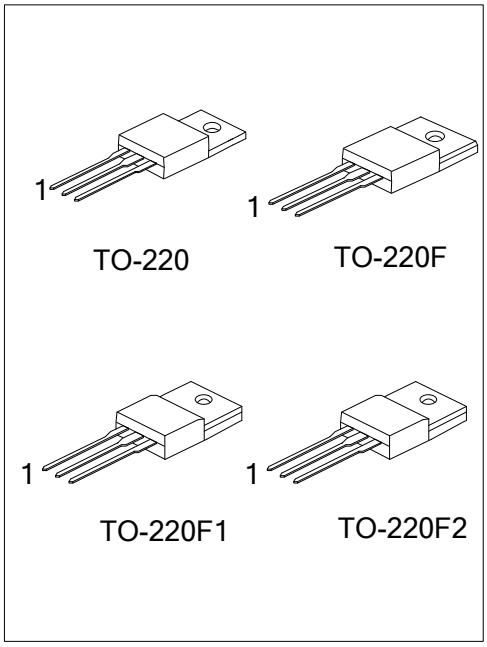
12A, 400V N-CHANNEL POWER MOSFET



■ DESCRIPTION

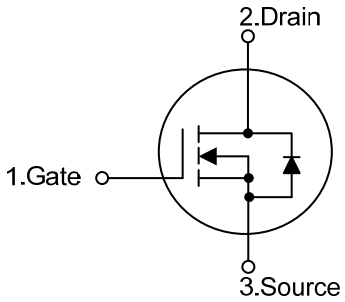
The UTC **12N40K-MT** is an N-channel mode power MOSFET using UTC' s advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **12N40K-MT** is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.

■ FEATURES

* $R_{DS(ON)}$ < 0.47Ω @ V_{GS} = 10 V, I_D = 12 A
* High switching speed
* 100% avalanche tested

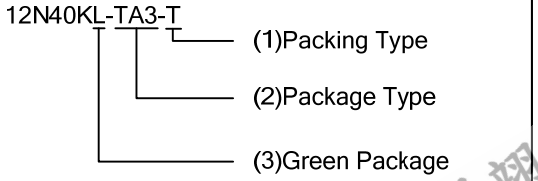
■ SYMBOL



■ ORDERING INFORMATION

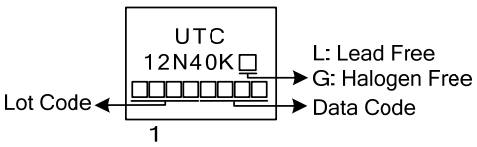
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12N40KL-TA3-T	12N40KG-TA3-T	TO-220	G	D	S	Tube
12N40KL-TF3-T	12N40KG-TF3-T	TO-220F	G	D	S	Tube
12N40KL-TF1-T	12N40KG-TF1-T	TO-220F1	G	D	S	Tube
12N40KL-TF2-T	12N40KG-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube
(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2
(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	400	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous (T_C=25°C)	I_D	12	A
	Pulsed (Note 2)	I_{DM}	48	A
Single Pulsed Avalanche Energy		E_{AS}	474	mJ
Power Dissipation	TO-220	P_D	135	W
	TO-220F/TO-220F1 TO-220F2		34	W
Derate above 25°C	TO-220		1.08	W/°C
	TO-220F/TO-220F1 TO-220F2		0.27	W/°C
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
4. L=7.27mH, I_{AS}=11A, V_{DD}= 50V, R_G=25Ω, Starting T_J=25°C
5. I_{SD} ≤11A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

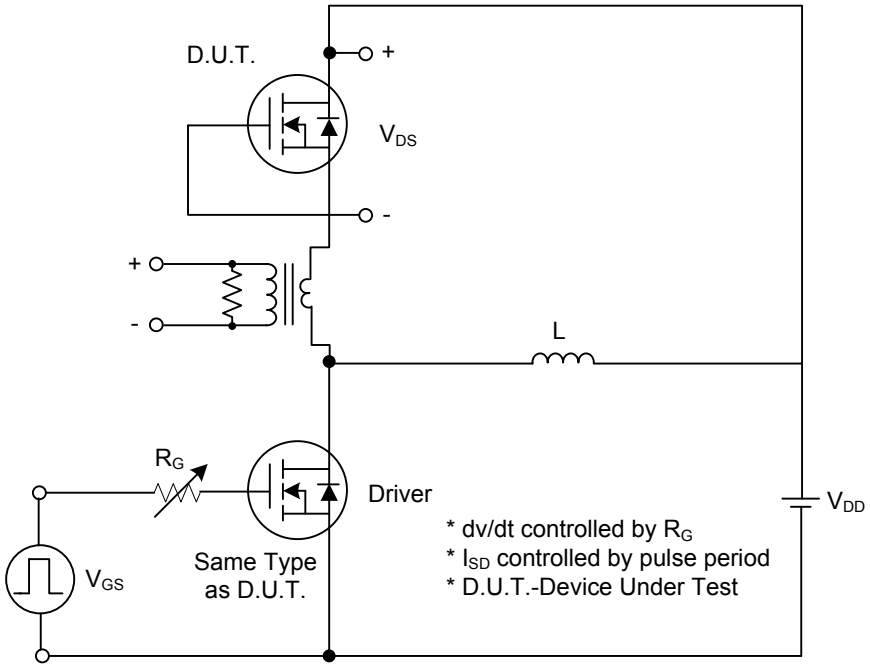
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220	θ_{JC}	0.92	°C/W
	TO-220F/TO-220F1 TO-220F2		3.7	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

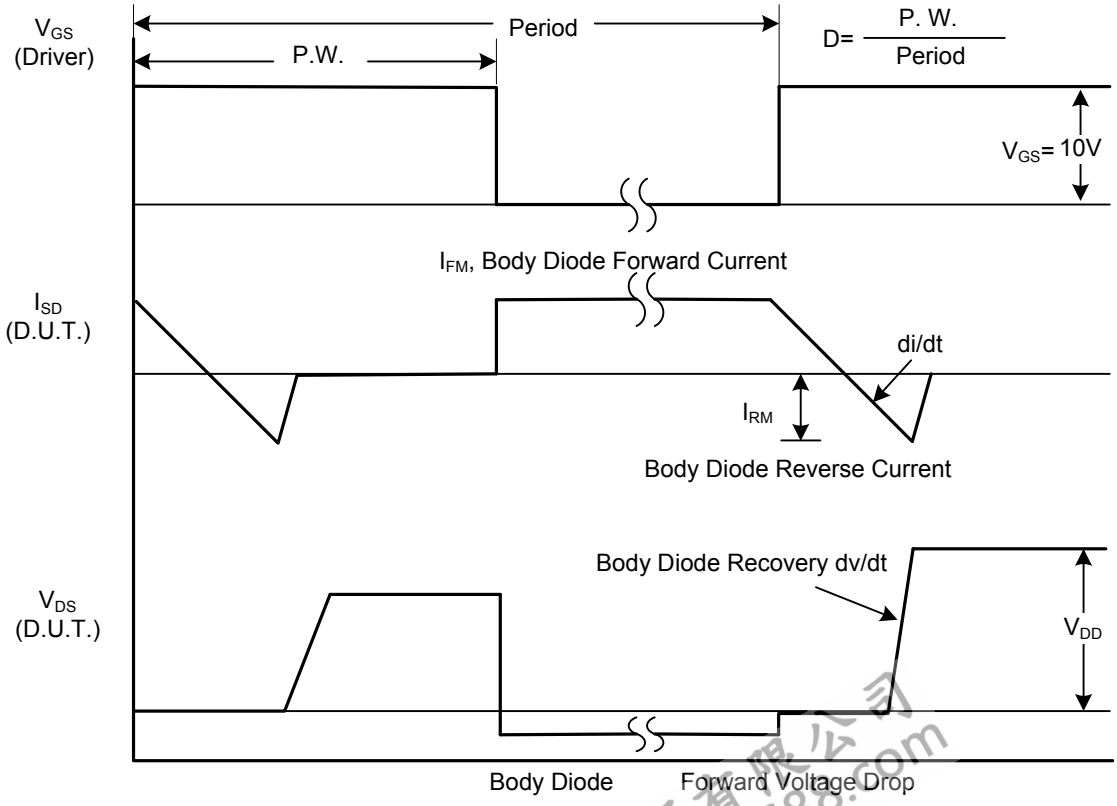
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	400			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=400V, V_{GS}=0V			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=12A			0.47	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		750		pF
Output Capacitance		C_{OSS}			153		pF
Reverse Transfer Capacitance		C_{RSS}			10		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}= 50V, V_{GS}= 10V, I_D= 0.3A, I_D=100μA (Note 1, 2)		31.3		nC
Gate-Source Charge		Q_{GS}			8.9		nC
Gate-Drain Charge		Q_{GD}			8.6		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DS}= 30V, V_{GS}= 10V, I_D = 0.3A, R_G = 25Ω (Note 1, 2)		62		ns
Rise Time		t_R			94		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			162		ns
Fall-Time		t_F			96		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	I_S=12A, V_{GS}=0V			1.4	V
Maximum Body-Diode Continuous Current		I_S				12	A
Maximum Body-Diode Pulsed Current		I_{SM}				48	A

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

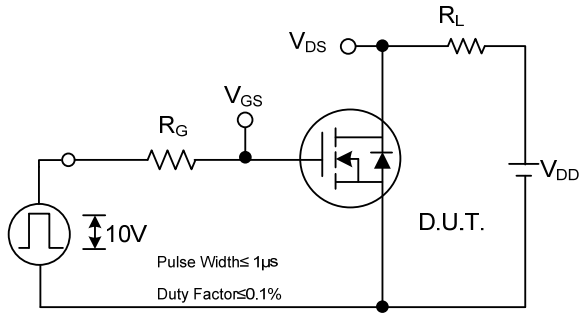


Peak Diode Recovery dv/dt Test Circuit

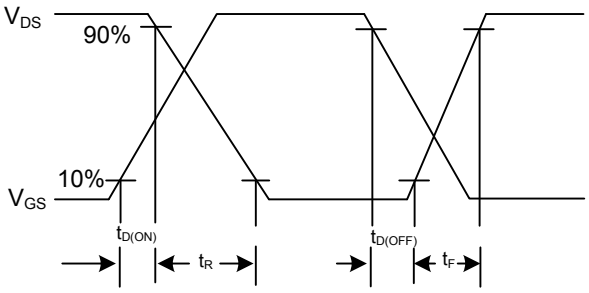


Peak Diode Recovery dv/dt Waveforms

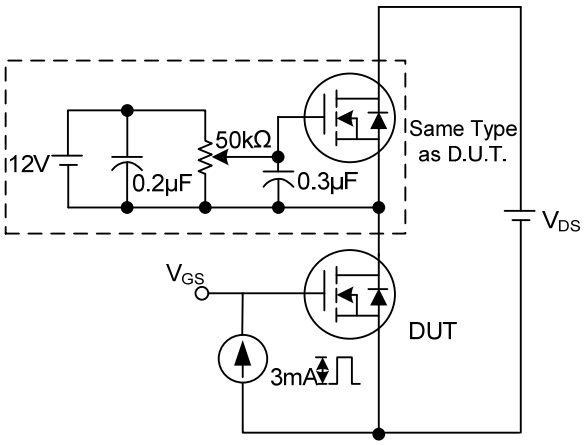
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



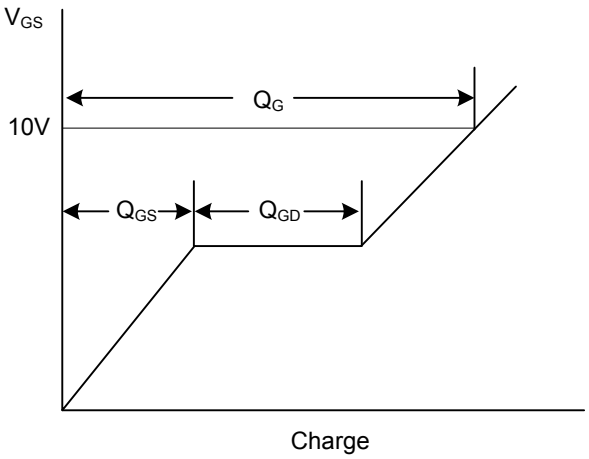
Switching Test Circuit



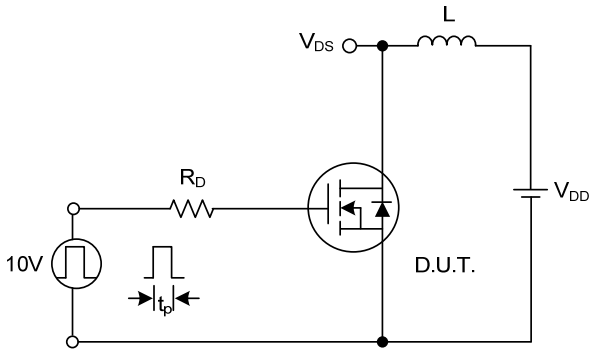
Switching Waveforms



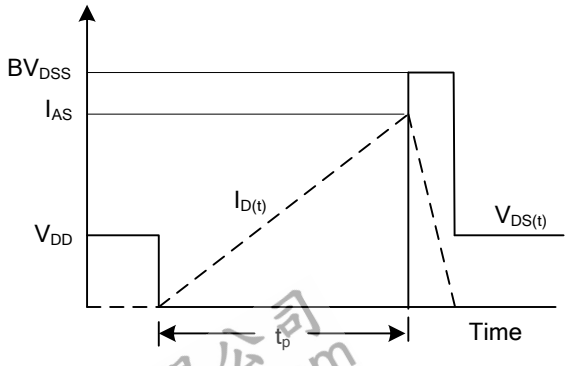
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms